

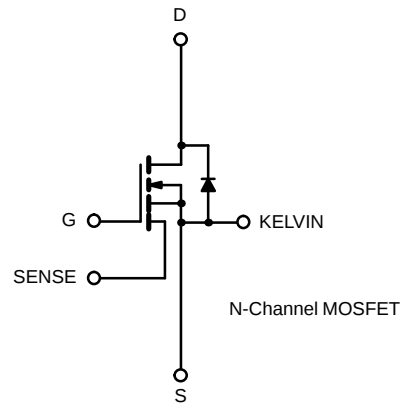
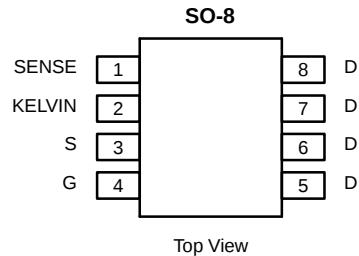


Current Sensing MOSFET, N-Channel 30-V (D-S)

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.015 @ $V_{GS} = 10$ V	11.7
	0.020 @ $V_{GS} = 4.5$ V	10.1

175°C Rated
Maximum Junction Temperature
TrenchFET®
Power MOSFETs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	11.7	8.0	A
	T _A = 70°C		9.8	6.7	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	40		
Continuous Source Current (Diode Conduction) ^a		I _S	3.3	1.6	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.6	1.7	W
	T _A = 70°C		2.5	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	35	42	$^\circ\text{C/W}$
	Steady State		77	90	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	18	22	

Notes

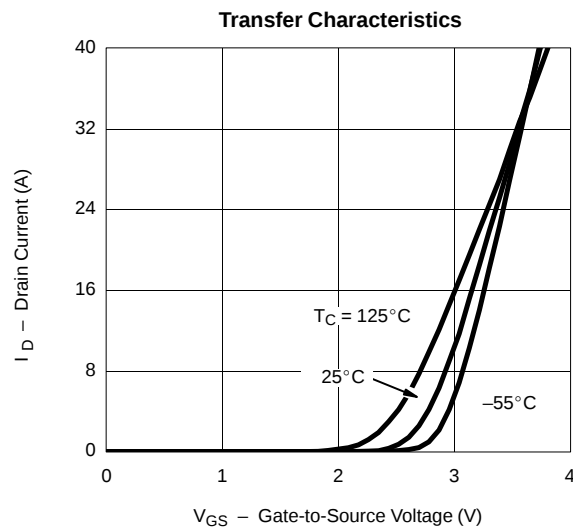
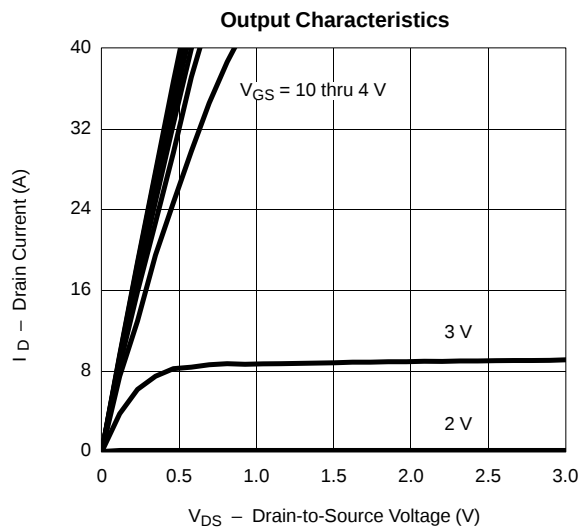
a. Surface Mounted on 1" x 1" FR4 Board.

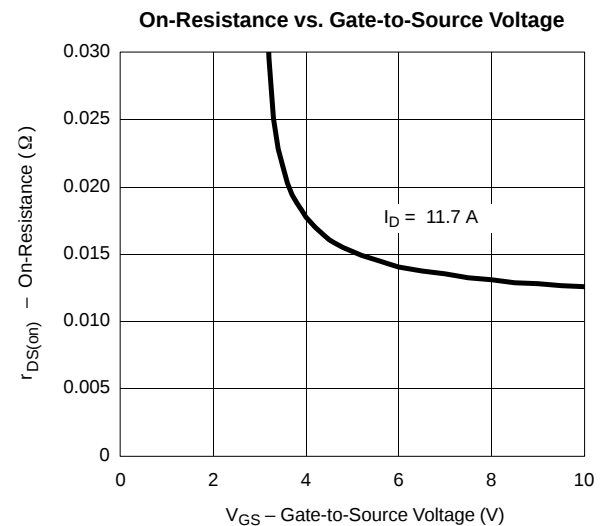
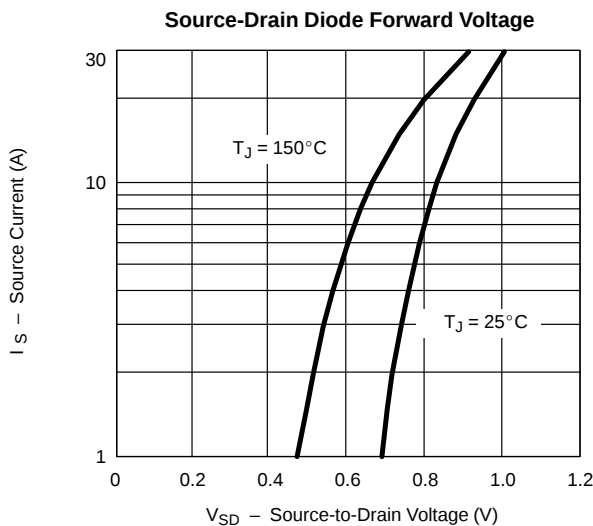
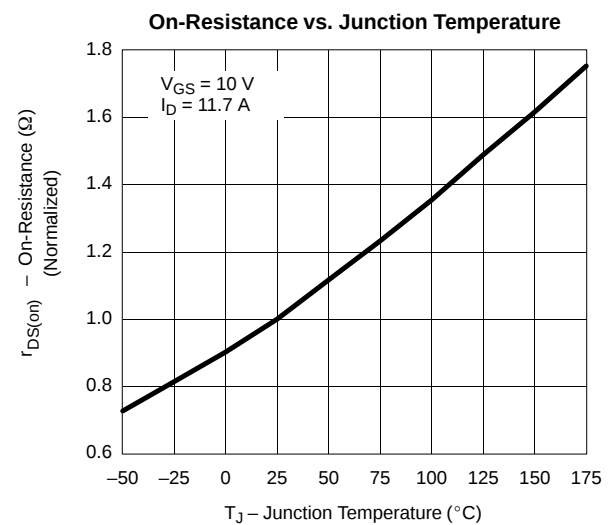
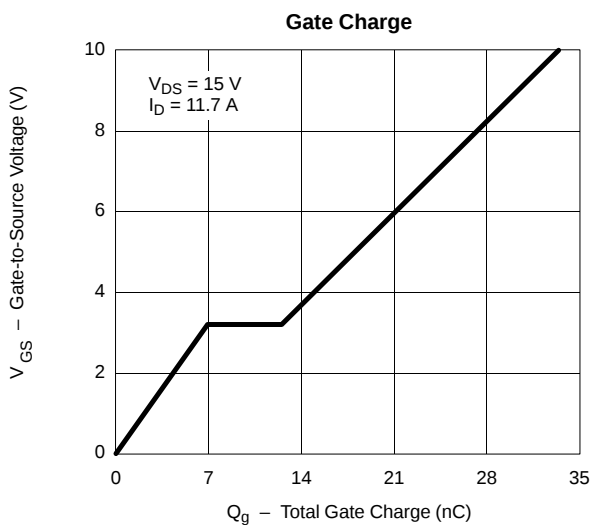
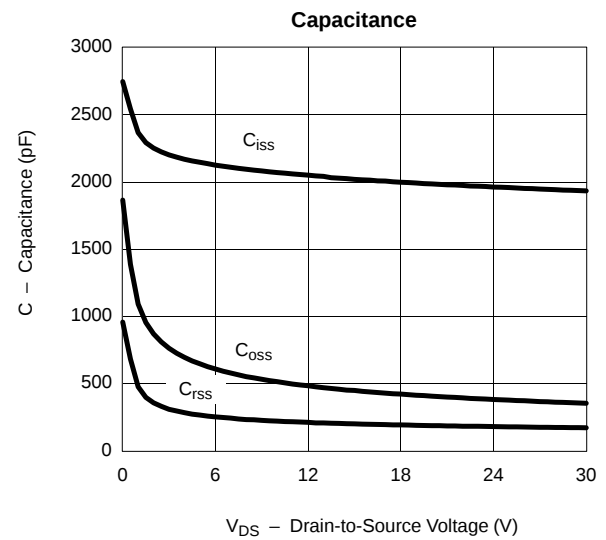
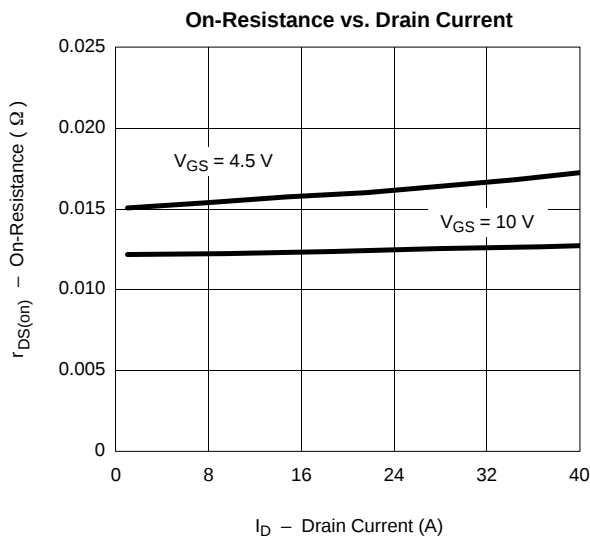
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

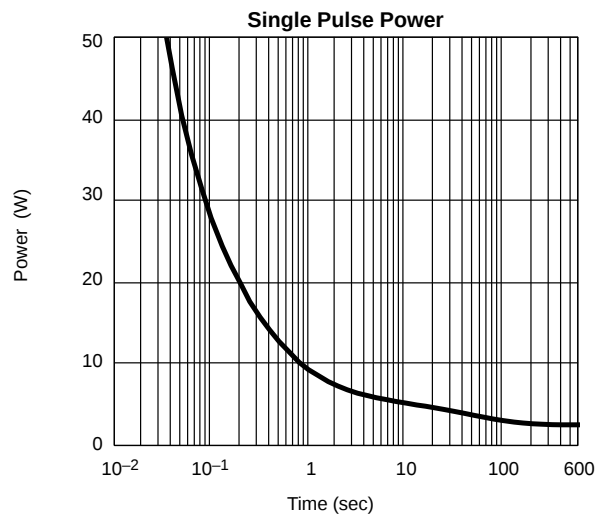
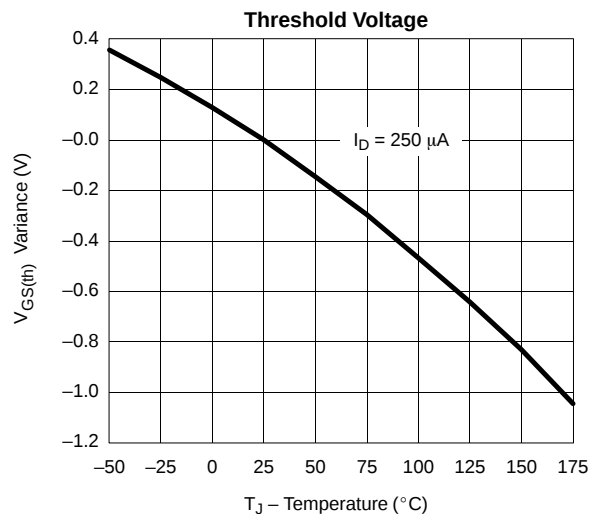
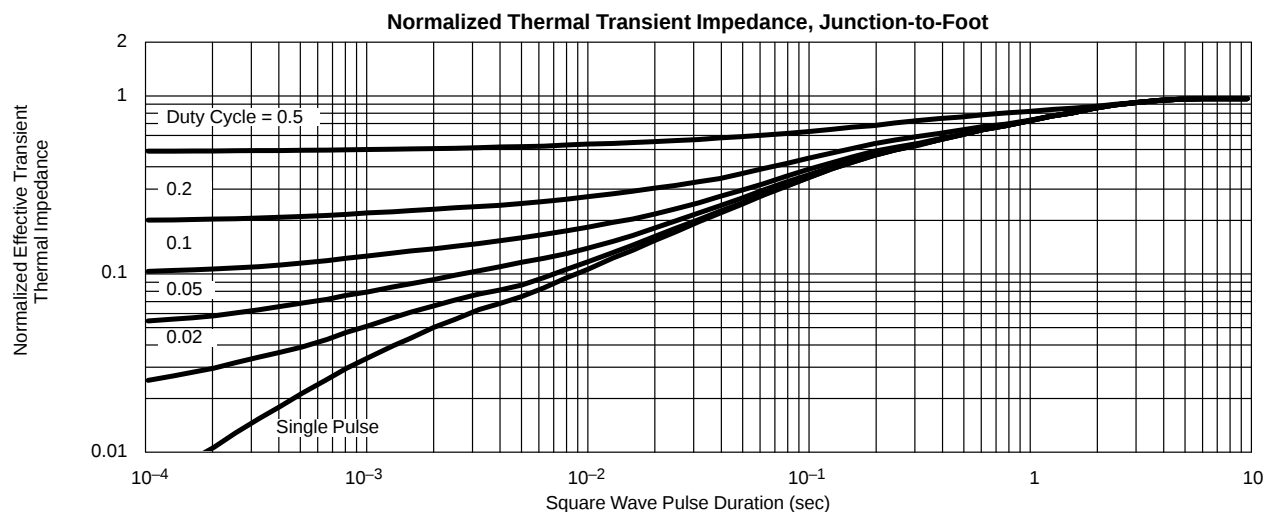
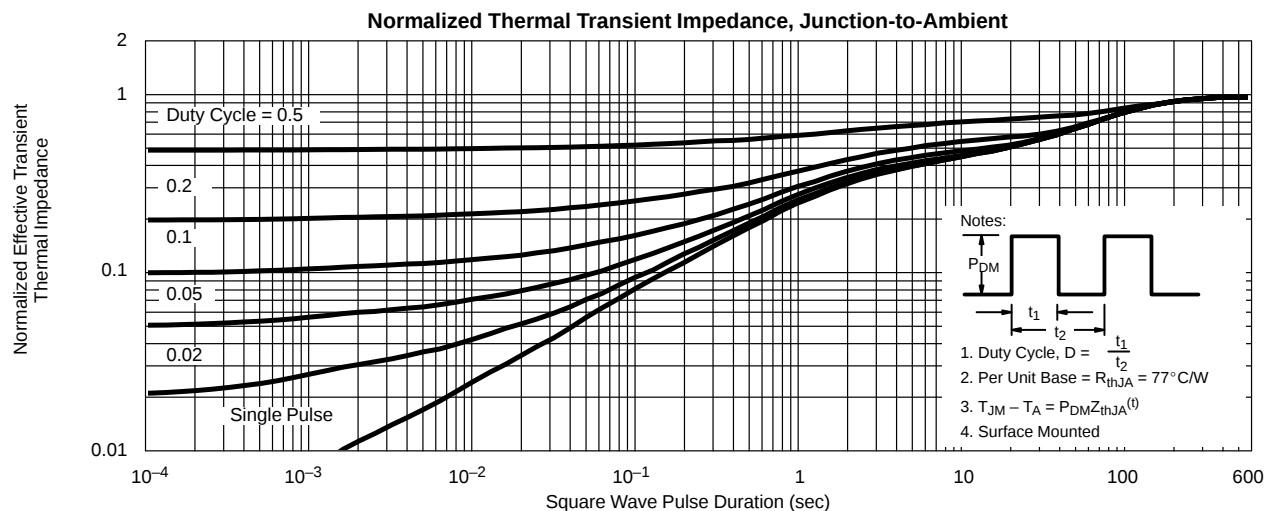
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 11.7\ \text{A}$		0.0125	0.015	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 10.1\ \text{A}$		0.015	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 11.7\ \text{A}$		35		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.3\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 11.7\ \text{A}$		34	50	nC
Gate-Source Charge	Q_{gs}			7		
Gate-Drain Charge	Q_{gd}			5.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		13	26	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			60	120	
Fall Time	t_f			20	40	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3.3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		30	60	
Current Sense Characteristics						
Current Sensing Ratio	r	$I_D = 1\ \text{A}$, $V_{GSS} = 10\ \text{V}$, $R_{SENSE} = 2.2\ \Omega$	360	450	540	
Mirror Active Resistance	$r_{m(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{mA}$		3.5		Ω

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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SENSE DIE

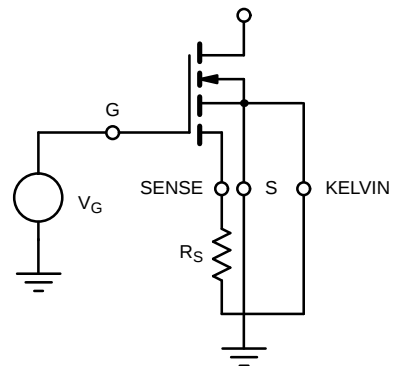
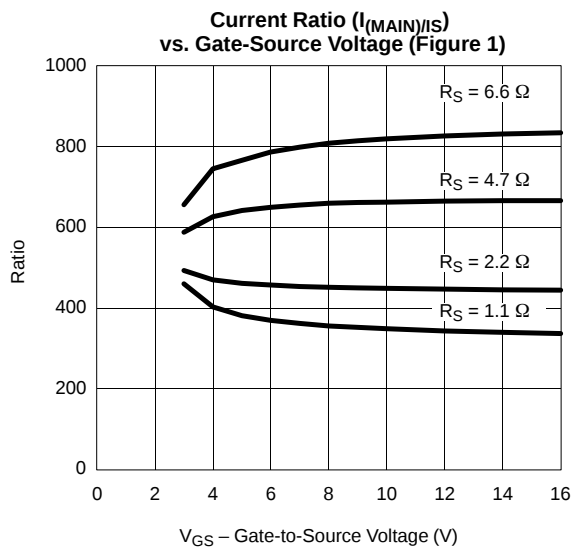
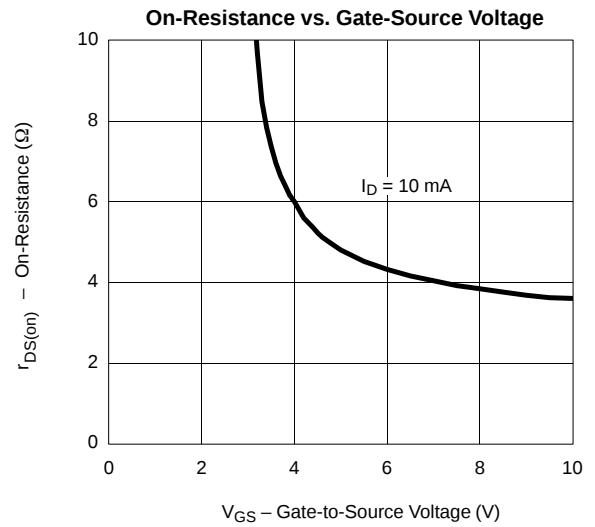
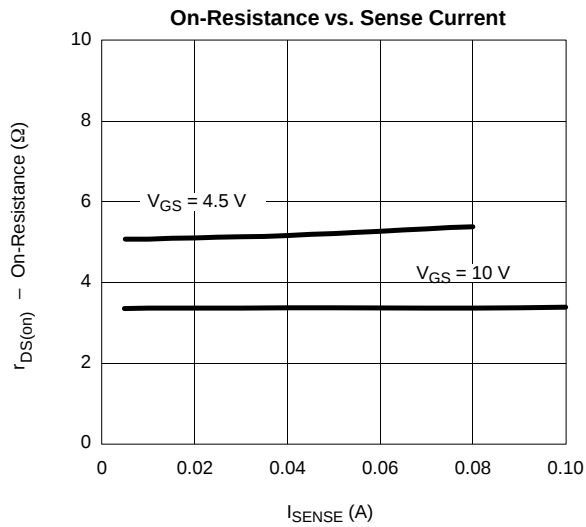


Figure 1